

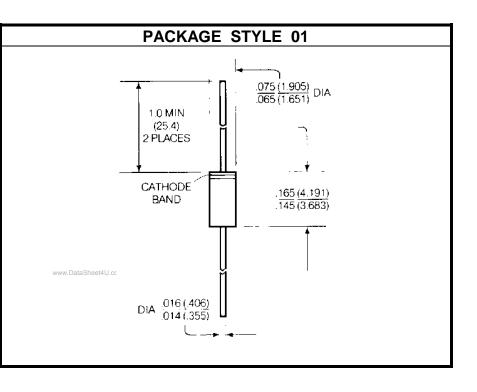
SILICON PIN DIODE CHIP

DESCRIPTION:

The **AP300A-00** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of Control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

MAXIMUM RATINGS

I _F	100 mA				
V_{R}	300 V				
P _{DISS}	250 mW @ $T_A = 25 \ ^{\circ}C$				



CHARACTERISTICS $T_C = 25 °C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V _{BR}	I _R = 10 μA	300			V
C	$\begin{array}{l} V_{R} = 50 \ V \\ V_{R} = 40 \ V \end{array} \qquad $			0.2	pF
Rs	I _F = 50 mA f = 100 MHz			0.6	Ohms
ΤL	$I_F = 10 \text{ mA}$ $I_R = 6.0 \text{ mA}$		1000		nS
T _{rr}	$I_{\rm F} = 20 \text{ mA}$ $I_{\rm R} = 100 \text{ mA}$		100		nS
O _R	THERMAL RESISTANCE			20	°C/W

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